



40V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET POWERDI®

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D T _C = +25°C	
40V	$2.5 \text{m}\Omega$ @ $V_{GS} = 10V$	100A	
400	4mΩ @ V _{GS} = 4.5V	100A	

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

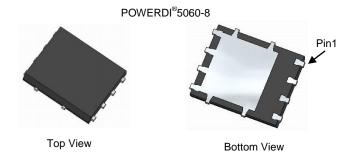
- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

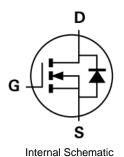
Features

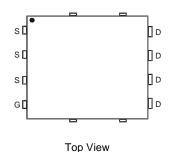
- Rated to +175°C ideal for high ambient temperature environments
- 100% Unclamped Inductive Switching ensures more reliable and robust end application
- Low R_{DS(ON)} minimizes power losses
- Low Qg minimizes switching losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: POWERDI[®]5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)







Pin Configuration

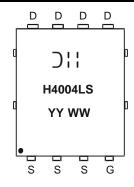
Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH4004LPS-13	POWERDI [®] 5060-8	2,500 / Tape & Reel

Notes:

- $1. \; EU \; Directive \; 2002/95/EC \; (RoHS) \; \& \; 2011/65/EU \; (RoHS \; 2) \; compliant. \; All \; applicable \; RoHS \; exemptions \; applied.$
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



);; = Manufacturer's Marking
H4004LS = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 14 = 2014)
WW = Week (01 to 53)

POWERDI is a registered trademark of Diodes Incorporated. DMTH4004 LPS



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		V_{DSS}	40	V
Gate-Source Voltage		V _{GSS}	±20	V
Continuous Drain Current (Note 5)	$T_A = +25$ °C $T_A = +70$ °C	ID	26 21	А
Continuous Drain Current (Note 6)	$T_C = +25$ °C $T_C = +70$ °C (Note 8)	I _D	100 100	А
Maximum Continuous Body Diode Forward Current (Note 6)	Is	70	Α	
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)		I _{DM}	100	Α
Avalanche Current, L=0.2mH		I _{AS}	33.3	Α
Avalanche Energy, L=0.2mH		E _{AS}	110	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	2.6	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	47	°C/W	
Total Power Dissipation (Note 6)	$T_C = +25^{\circ}C$	P _D	138	W
Thermal Resistance, Junction to Case (Note 6)		R _{eJC}	0.9	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +175	°C

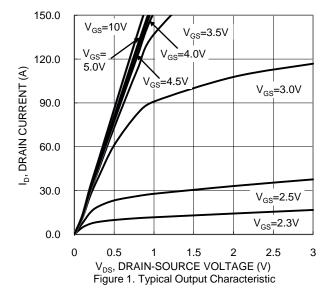
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

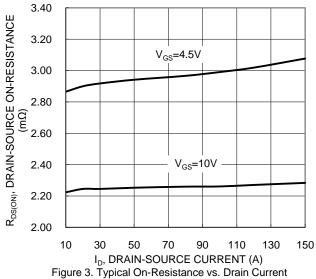
D-							
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	40	_	_	V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 32V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	1	_	3	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance		_	_	2.5	mΩ	$V_{GS} = 10V, I_D = 50A$	
Static Dialii-Source Off-Resistance	R _{DS(ON)}	-	_	4	11122	$V_{GS} = 4.5V, I_D = 50A$	
Diode Forward Voltage	V _{SD}	_	0.9	1.2	V	$V_{GS} = 0V, I_{S} = 50A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	1	4508	_		V_{DS} = 20V, V_{GS} = 0V, f = 1MHz	
Output Capacitance	Coss	_	1648	_	pF		
Reverse Transfer Capacitance	C _{rss}	1	104	_			
Gate Resistance	Rg	_	0.7	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	-	34.6	_	nC		
Total Gate Charge (V _{GS} = 10V)	Qg	1	82.2	_		V 20V I- 20A	
Gate-Source Charge	Q_{gs}	_	9.9	_	nC	$V_{DD} = 20V, I_D = 30A$	
Gate-Drain Charge	Q_{gd}	1	11.2	_			
Turn-On Delay Time	t _{D(ON)}	_	5.9	_		$V_{DD} = 20V, V_{GS} = 10V,$ $I_{D} = 30A, R_{G} = 1.6\Omega$	
Turn-On Rise Time	t _R	_	13.3	_	20		
Turn-Off Delay Time	t _{D(OFF)}	_	25.9	_	ns		
Turn-Off Fall Time	t _F	_	7.9	_			
Body Diode Reverse Recovery Time	t _{RR}		48.4	_	ns	I 50A di/dt _ 100A/ug	
Body Diode Reverse Recovery Charge	Q _{RR}		72.4	_	nC	$I_F = 50A$, di/dt = 100A/ μ s	

Notes:

- 5. Device mounted with exposed drain pad on 25mm by 25mm 2oz copper on a single- sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady state.
- 6. Thermal resistance from junction to soldering point (on the exposed drain pad).
 7 .Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to production testing.







and Gate Voltage

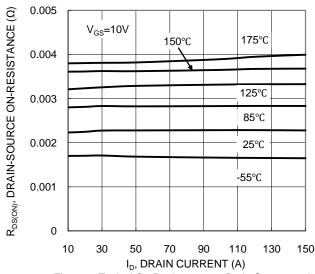
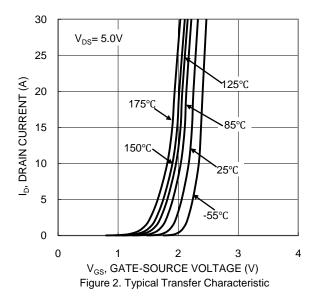
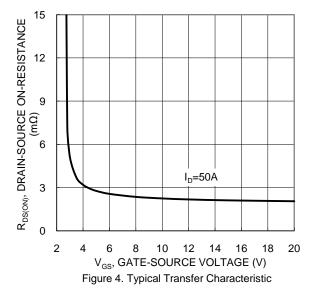
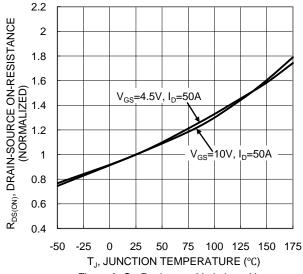


Figure 5. Typical On-Resistance vs. Drain Current and Temperature









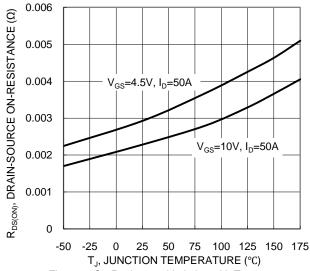
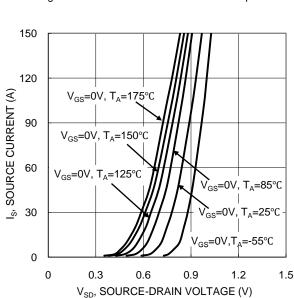
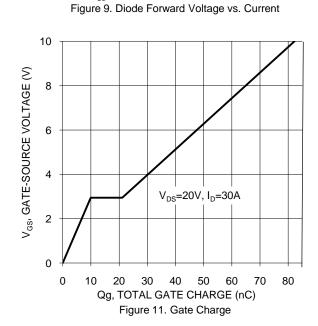


Figure 7. On-Resistance Variation with Temperature





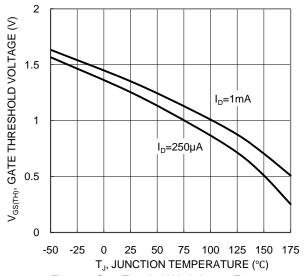
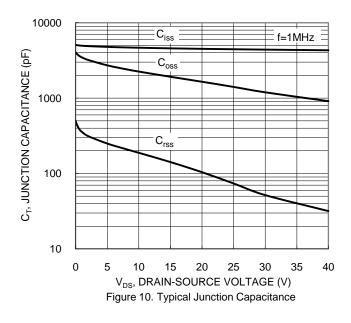
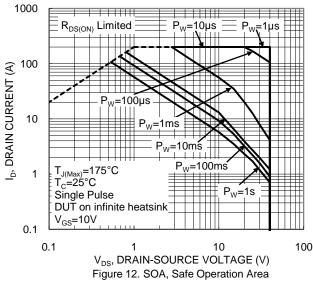


Figure 8. Gate Threshold Variation vs. Temperature







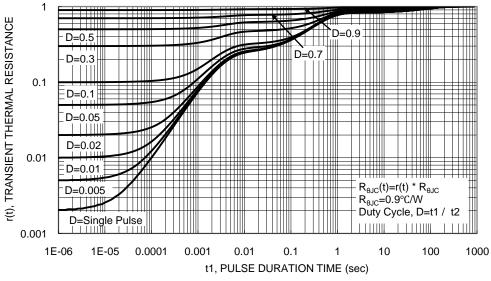
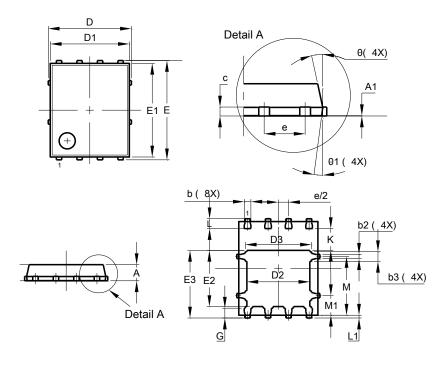


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



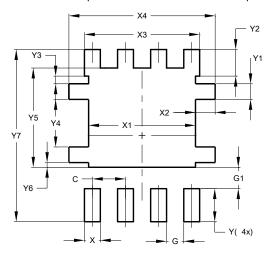
POWERDI®5060-8						
Dim	Min	Max	Тур			
Α	0.90	1.10	1.00			
A1	0.00	0.05	-			
b	0.33	0.51	0.41			
b2	0.200	0.350	0.273			
b3	0.40	0.80	0.60			
С	0.230	0.330	0.277			
D	Ļ	5.15 BSC	;			
D1	4.70	5.10	4.90			
D2	3.70	4.10	3.90			
D3	3.90	4.30	4.10			
Е	•	6.15 BSC				
E1	5.60	6.00	5.80			
E2	3.28	3.68	3.48			
E3	3.99	4.39	4.19			
е	1.27 BSC					
G	0.51	0.71	0.61			
K	0.51	-	-			
L	0.51	0.71	0.61			
L1	0.100	0.200	0.175			
M	3.235	4.035	3.635			
M1	1.00	1.40	1.21			
θ	10°	12º	11º			
θ1	6°	80	7º			
All Dimensions in mm						

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Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
Х	0.610
X1	4.100
X2	0.755
Х3	4.420
X4	5.610
Υ	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

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